

Thermoelectricity: From Atoms to Systems

Week 5: Recent Advances in Materials and Physics Lecture 5.2: Semiconductors with embedded nanoparticles

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Semimetallic nanoparticles: ErAs/III-V (Quest



Semimetal ErAs (Rock-salt) a=5.74 Å

Semiconductor e.g. InGaAlAs (Zinc blende) a=5.85 Å

- Arsenic has a continuous fcc sublattice.
- ErAs is a Rock-salt semi metal, ~ lattice matched to InGaAIAs



A.G. Petukhov, et. al. Phys. Rev. B. 53(8), 1996.

J. Zide and A. Gossard (UCSB)



ErAs Semi-metal Nanoparticles imbedded in InGaAs Semiconductor Matrix

➤ Erbium is co-deposited at a growth rate which is a fixed fraction of the InGaAs growth rate (MBE growth, 60 microns thick films)
➤ Solubility limit is exceeded → nanoparticles are formed (2-3nm)





HAADF/STEM of ErAs Nanoparticles



STEM: ErAs particles have the rock salt structure. The As sublattice is continuous across the interface.

D. O. Klenov, D. C. Driscoll, A. C. Gossard, S. Stemmer, Appl. Phys. Lett. 86, 111912 (2005)





Beating the Alloy Limit in Thermal Conductivity



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Modeling of thermal conductivity



Kim and Majumdar, Journal of Applied Physics, 99, 084306 (2006)



Nanoparticle scattering cross section



 $\ell = \frac{1}{\sigma\eta}$

- σ : Scattering cross section
- η : Impurity concentration

$$\sigma = \int_{0}^{\infty} \sigma_{sct} \begin{pmatrix} size \\ distribution \\ function \\ mean(d_{M}) \\ standard deviation(\sigma) \end{pmatrix} dr$$



• qR : Size parameter, χ

Kim and Majumdar, Journal of Applied Physics, 99, 084306 (2006)



Using Nanoparticles to Reduce Lattice Thermal Conductivity





Electrical Properties of ErAs:InGaAlAs



- ErAs e e ErAs e e e ErAs e e e ErAs InGaAs
- The Fermi levels of nanocomposites depend on the semiconductor matrix.
 - For example, the Fermi level in ErAs:GaAs is pinned deep within the bandgap.
- ErAs contributes electrons to InGaAs.
- Electron mobilities are high in ErAs:InGaAs.

Normalized ZT of 0.3% ErAs: InGaAs (300K)



W. Kim, J. Zide et al. Physical Review Letters 2006





Electrical conductivity and Seebeck (theory/experiment)





M. Zebarjadi, et al., Appl. Phys. Lett. 2009 J.-H. Bahk et al., Phys. Rev. B 2010 (Si-doped) J. Zide et al., J. Appl. Phys. 2010

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Embedded nanoparticle scattering



Born Approximation



- Perturbation theory
- Point size potentials

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Low barriers

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Partial Wave technique



- Exact solution of Schrodinger
- Finite size scattering center
- Harder to implement

Mona Zebarjadi, et al. Appl. Phys. Lett. 94: 202105, 2009

Multiple scatterings => Coherent Potential Approximation (not described here, M. Zebarjadi, et al. Nano Letters, 11, 225, 2011)

Mobility (Theory vs. Experiment)



Electron mobility in embedded nanoparticle material





Je-Hyeong Bahk, Peter Burke, et al. 2013

Seebeck (Theory vs. Experiment)



Scattering mechanisms:

Polar optical phonons Acoustic phonons Intervalley phonons Impurity Alloy scattering Nano particle scattering: (Partial Wave technique)

Solid lines are theoretical pr ediction (no fitting)

Je-Hyeong Bahk, Mona Zebarjadi et al. (2009)

Thermoelectric figure-of-merit





The majority of ZT enhancement is from thermal conductivity reduction. 5% power factor enhancement at 800K.

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Nanoparticle scattering optimization



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Cross-plane and in-plane Seebeck in thick barrier superlattices InGaAs:ErAs/InGaAIAs

Enhance energy filtering by inserting InGaAlAs barriers inside ErAs: InGaAs can enhance cross-plane Seebeck by a factor of 3



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Nanoparticle in alloy for thermal conductivity reduction



3.4% nanoparticles





Week 5: Lecture 2 Summary



- Embedded ErAs nanoparticles in InGaAs (endo-epitaxial nanoparticles –see Kanatzidis group)
- Thermal conductivity reduction below alloy limit
 - Long/mid wavelength phonon scattering
- Power factor enhancement
 - improved mobility -modulation doping
 - Energy filtering (?) –scattering time has sharper energy dependence

